20 V, 2 A PNP medium power transistors

Rev. 8 — 12 December 2024

Product data sheet

1. General description

PNP medium power transistor in a SOT89 (SC-62) medium power and flat lead plastic package.

2. Features and benefits

- High current
- Three current gain selections
- · High power dissipation capability
- Exposed heatsink for excellent thermal and electrical conductivity
- Leadless very small SMD plastic package with medium power capability
- AEC-Q101 qualified

3. Applications

- Linear voltage regulators
- High-side switches
- Battery-driven devices
- Power management
- MOSFET drivers
- **Amplifiers**

4. Quick reference data

Table 1. Quick reference data

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	-20	V
I _C	collector current			-	-	-2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-3	А
h _{FE}	DC current gain						
	BC869	V _{CE} = -1 V; I _C = -500 mA	[1]	85	-	375	
	BC869-16	T _{amb} = 25 °C	[1]	100	-	250	
	BC869-25		[1]	160	-	375	

[1] pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$



20 V, 2 A PNP medium power transistors

5. Pinning information

Table 2. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	E	emitter		B —
3	С	collector		
			$\overline{3}$ $\overline{2}$ $\overline{1}$	E
				006aaa231

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BC869	-	plastic thermal enhanced ultra thin small outline package; no	SOT89			
BC869-16		leads; 3 terminals; body 2 x 2 x 0.65 mm				
BC869-25						

7. Marking

Table 4. Marking

Type number	Marking code
BC869	CEC
BC869-16	CGC
BC869-25	CHC

20 V, 2 A PNP medium power transistors

8. Limiting values

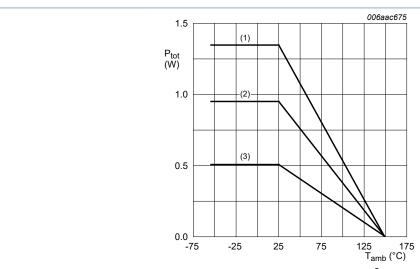
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-32	V
V _{CEO}	collector-emitter voltage	open base		-	-20	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-3	Α
I _B	base current			-	-0.4	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-0.4	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.50	W
			[2]	-	0.95	W
			[3]	-	1.35	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- Device mounted on an FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm². Device mounted on an FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 6 cm².



- (1) FR4 PCB, single-sided copper, mounting pad for collector 6 cm²
- (2) FR4 PCB, single-sided copper, mounting pad for collector 1cm²
- (3) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves

20 V, 2 A PNP medium power transistors

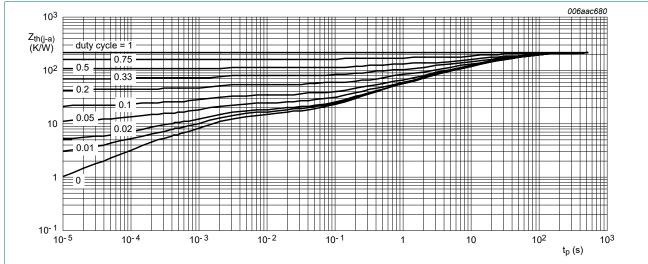
9. Thermal characteristics

Table 6. Thermal characteristics

 T_{amb} = 25 °C unless otherwise specified.

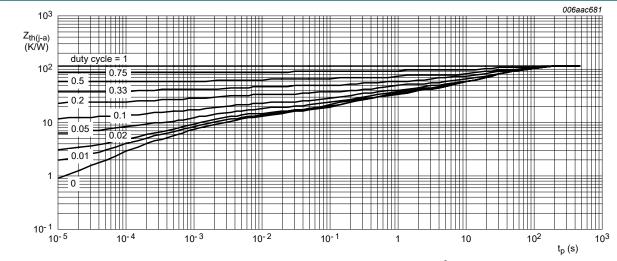
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W
			[2]	-	-	132	K/W
			[3]	-	-	93	K/W
R _(j-sp)	thermal resistance from junction to solder point			-	-	16	K/W

- 1] Device mounted on an FR4 PCB; single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 6 cm².



FR4 PCB; single-sided copper; tin-plated and standard footprint

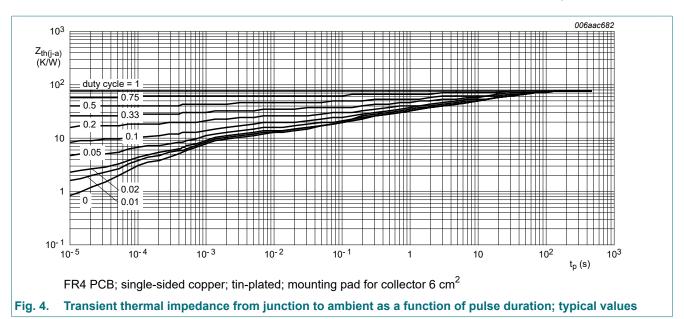
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm²

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, 2 A PNP medium power transistors



20 V, 2 A PNP medium power transistors

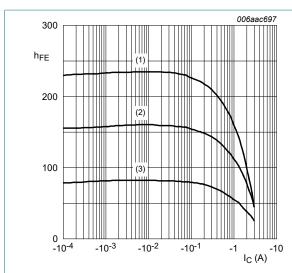
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{СВО}	collector-base cut-off current	V _{CB} = -25 V; I _E = 0 A T _{amb} = 25 °C		-	-	-100	nA
		V _{CB} = -25 V; I _E = 0 A; T _j = 150 °C		-	-	-10	μΑ
ЕВО	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A T _{amb} = 25 °C		-	-	-100	nA
ηFE	DC current gain				'	'	
	BC869	V _{CE} = -10 V; I _C = -5 mA T _{amb} = 25 °C	[1]	50	-	-	
		V _{CE} = -1 V; I _C = -500 mA T _{amb} = 25 °C	[1]	85	-	375	
		V _{CE} = -1 V; I _C = -1 A T _{amb} = 25 °C	[1]	60	-	-	
		V _{CE} = -1 V; I _C = -2 A T _{amb} = 25 °C	[1]	40	-	-	
	BC869-16	V _{CE} = -10 V; I _C = -5 mA T _{amb} = 25 °C	[1]	50	-	-	
		V _{CE} = -1 V; I _C = -500 mA T _{amb} = 25 °C	[1]	100	-	250	
		V _{CE} = -1 V; I _C = -1 A T _{amb} = 25 °C	[1]	60	-	-	
		V _{CE} = -1 V; I _C = -2 A T _{amb} = 25 °C	[1]	40	-	-	
	BC869-25	V _{CE} = -10 V; I _C = -5 mA T _{amb} = 25 °C	[1]	50	-	-	
		V_{CE} = -1 V; I_{C} = -500 mA T_{amb} = 25 °C	[1]	160	-	375	
		V _{CE} = -1 V; I _C = -1 A T _{amb} = 25 °C	[1]	60	-	-	
		V _{CE} = -1 V; I _C = -2 A T _{amb} = 25 °C	[1]	40	-	-	
V_{CEsat}	collector-emitter saturation voltage	I _C = -1 A; I _B = -100 mA T _{amb} = 25 °C	[1]	-	-	-0.5	V
		I _C = -2 A; I _B = -200 mA T _{amb} = 25 °C	[1]	-	-	-0.6	V
V_{BE}	base-emitter voltage	V _{CE} = -10 V; I _C = -5 mA T _{amb} = 25 °C	[1]	-	-	-0.7	V
		V _{CE} = -1 V; I _C = -1 A T _{amb} = 25 °C	[1]	-	-	-1	V
C _c	collector capacitance	V _{CB} = -10 V; I _E = i _e = 0 A; f = 1 MHz T _{amb} = 25 °C		-	28	-	pF
T	transition frequency	V _{CE} = -5 V; I _C = -50 mA; f = 100 MHz T _{amb} = 25 °C		40	140	-	MHz

^[1] pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02$

20 V, 2 A PNP medium power transistors

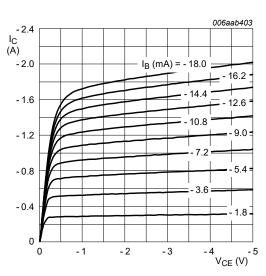


$$V_{CE} = -1 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

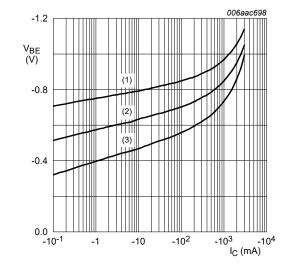
(3)
$$T_{amb} = -55$$
 °C

Fig. 5. hFE selection -16: DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 6. hFE selection -16: Collector current as a function of collector-emitter voltage; typical values



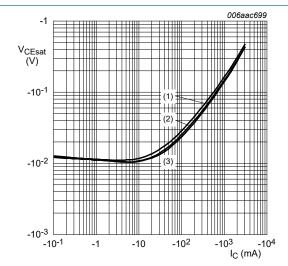
$$V_{CE} = -1 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. hFE selection -16: Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

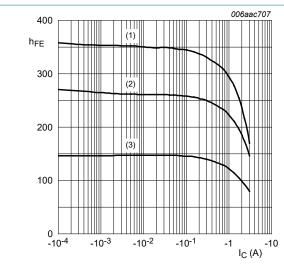
(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. hFE selection -16: Collector-emitter saturation voltage as a function of collector current; typical values

20 V, 2 A PNP medium power transistors



$$V_{CE} = -1 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 9. hFE selection -25: DC current gain as a function of collector current; typical values

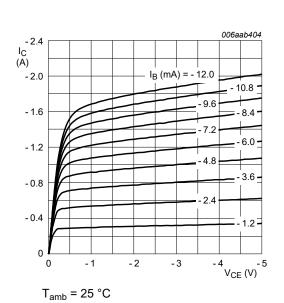
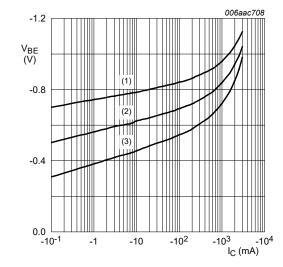


Fig. 10. hFE selection -25: Collector current as a function of collector-emitter voltage; typical values



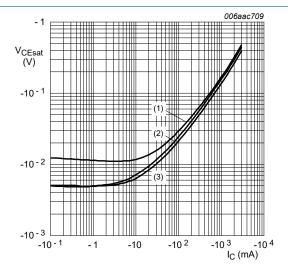
$$V_{CE} = -1 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 11. hFE selection -25: Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

Fig. 12. hFE selection -25: Collector-emitter saturation voltage as a function of collector current; typical values

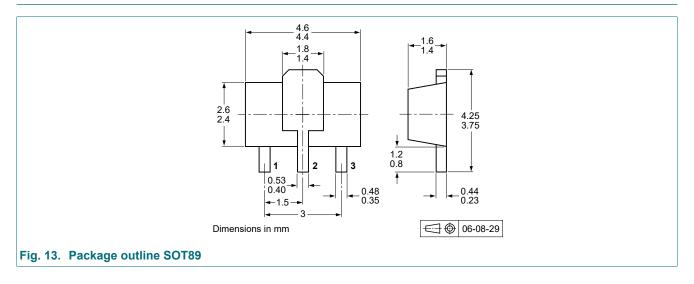
20 V, 2 A PNP medium power transistors

11. Test information

11.1. Quality information

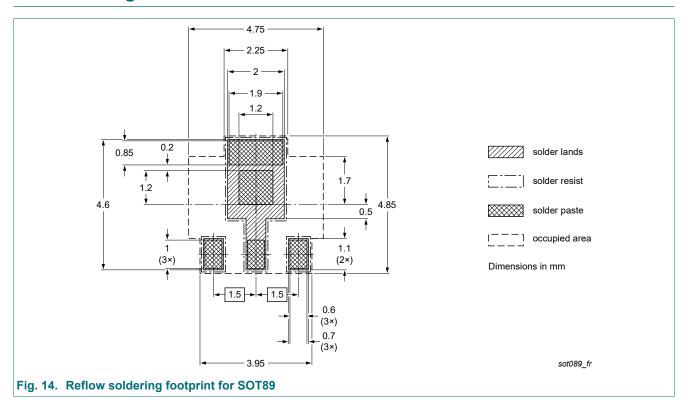
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

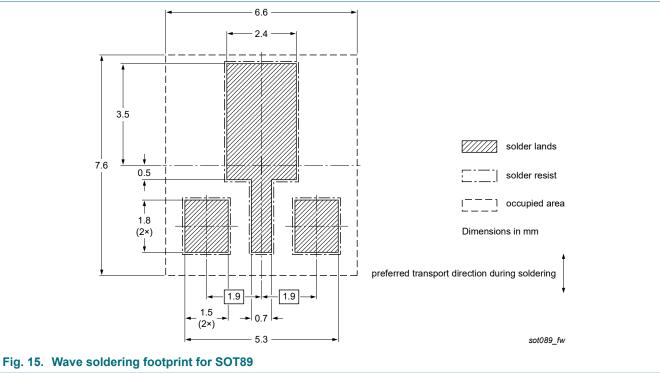
12. Package outline



20 V, 2 A PNP medium power transistors

13. Soldering





20 V, 2 A PNP medium power transistors

14. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC869_SER v.8	20241212	Product data sheet	-	BCP69_BC869_BC69PA v.7
Modifications:	· ·	arated into 3 data sheets g information" removed		
BCP69_BC869_BC69PA v.7	20111012	Product data sheet	-	BC869_6 BCP69_6
BC869_6	20041108	Product data sheet	-	BC869_5
BC869_5	20031202	Product specification	-	BC869_4
BC869_4	19990408	Product specification	-	BC869_3
BC869_3	19980716	Product specification	-	BC869_CNV_2
BC869_CNV_2	19970401	Product specification	-	-
BCP69_6	20081202	Product data sheet	-	BCP69_5
BCP69_5	20031125	Product specification	-	BCP69_4
BCP69_4	20021115	Product specification	-	BCP69_3
BCP69_3	19990408	Product specification	-	BCP69_CNV_2
BCP69_CNV_2	19970312	Product specification	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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20 V, 2 A PNP medium power transistors

Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	4
10. Characteristics	6
11. Test information	9
11.1. Quality information	9
12. Package outline	9
13. Soldering	10
14. Revision history	11
15. Legal information	12

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